

# **JEDEC STANDARD**

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## **Addendum No. 1 to JESD79-4, 3D Stacked DRAM**

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### **JESD79-4-1B**

(Revision of JESD79-4-1A, March 2020)

**February 2021**

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**ADDENDUM No. 1 to JESD79-4, 3D STACKED SDRAM**

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## ADDENDUM No. 1 to JESD79-4, 3D STACKED SDRAM

(From JEDEC Board Ballots JCB-16-29, JCB-19-34, and JCB-21-08 formulated under the cognizance of the JC-42.3C Subcommittee on DRAM Parametrics.)

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### 1 Scope

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This document defines the 3DS DDR4 SDRAM specification, including features, functionalities, AC and DC characteristics, packages, and ball/signal assignments. The purpose of this specification is to define the minimum set of requirements for a compliant 8 Gbit through 128 Gbit for x4, x8 3DS DDR4 SDRAM devices. This addendum was created based on the JESD79-4 DDR4 SDRAM specification. Each aspect of the changes for 3DS DDR4 SDRAM operation was considered. Any TBD's, as of the publication of this document, are under discussion by the formulating committee.

The requirement for 3DS devices compliant to this spec addendum is to have a single electrical load for the stacked devices no matter if the stack is comprised of 2, 4 or 8 devices. The I/O buffer circuitry can be built into the base SDRAM of the stack or into a separate logic buffer device. In either case (built in native circuitry or separate logic die), the assumption is that the I/O buffers are located at the bottom of the stack closest to the package substrate. All pictures and diagrams in the spec depict a primary die at the bottom of the stack; it is associated with logical rank 0.

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### 2 3DS SDRAM Package Pinout and Addressing

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#### 2.1 Overview

These ballouts have been derived from JESD79-4. The ballout comprehends x4 and x8 data widths, where x4 is a subset of the x8 ballout, and the addressing described in this section.

#### 2.2 Pinout Description

The following table only documents differences of DDR4 3DS SDRAMs relative to the pinout description in JESD79-4.

Symbol	Type	Function
PAR	Input	Command and Address Parity Input : DDR4 Supports Even Parity check in DRAMs with MR setting. Once it's enabled via Register in MR5, then DRAM calculates Parity with ACT_n,RAS_n/A16,CAS_n/A15,WE_n/A14,BG0-BG1,BA0-BA1,A17-A0 and C0, C1, C2. Input parity should maintain at the rising edge of the clock and at the same time with command and address with CS_n LOW

NOTE 1 Input only pins (BG0-BG1,BA0-BA1, A0-A17, ACT\_n, RAS\_n/A16, CAS\_n/A15, WE\_n/A14, CS\_n, CKE, ODT, C0, C1, C2 and RESET\_n) do not supply termination.

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